



YJP130G10B

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
		V _{DS} =100V, V _{GS} =0V, T _J =150°C	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	2.8	4	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =65A	-	4.5	5.5	m
		V _{GS} =10V, I _D =20A	-	4.5	5.5	
Diode Forward Voltage	V _{SD}	I _S =65A, V _{GS} =0V	-	0.9	1.2	V
Gate resistance	R _G	f=1MHz, Open drain	-	0.8	-	
Maximum Body-Diode Continuous Current	I _S		-	-	130	A
Dynamic Parameters						
Input Capacitance	C _{iss}					

V



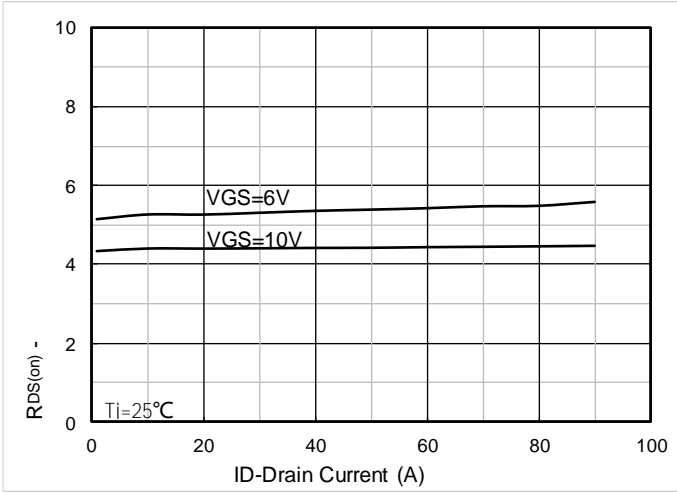


Figure7. RDS(on) VS Drain Current



Figure8. Forward characteristics of reverse diode

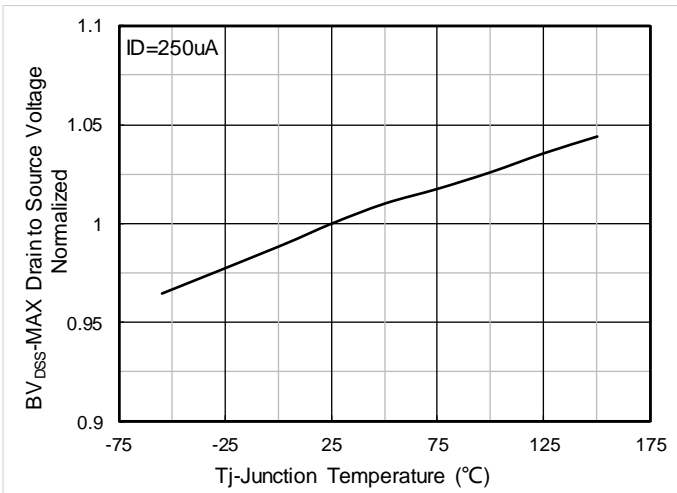


Figure9. Normalized breakdown voltage

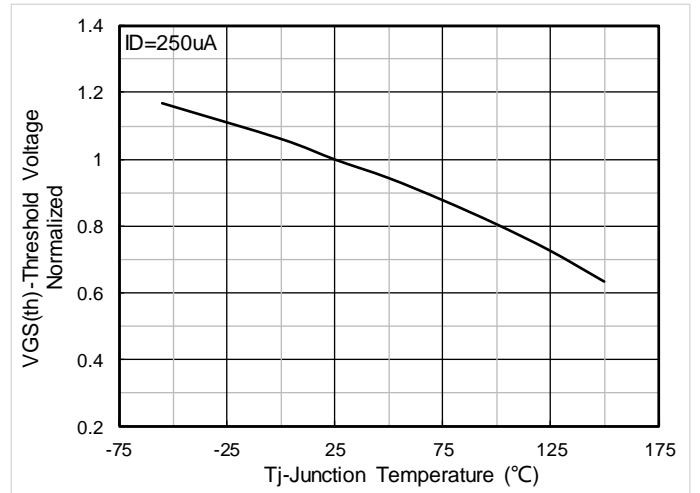


Figure10. Normalized Threshold voltage

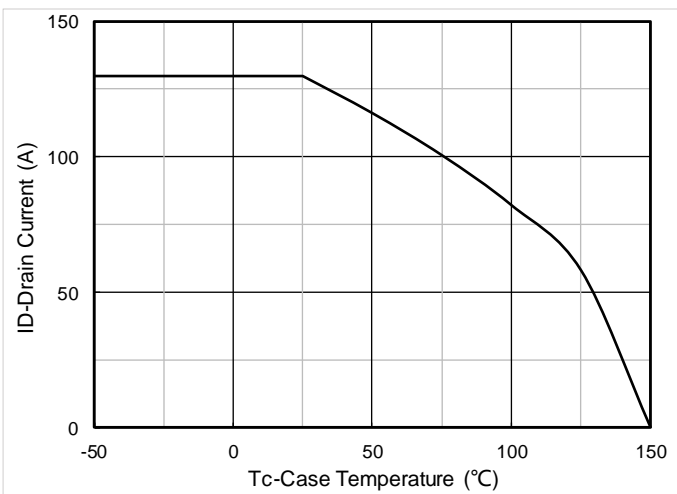


Figure11. Current dissipation

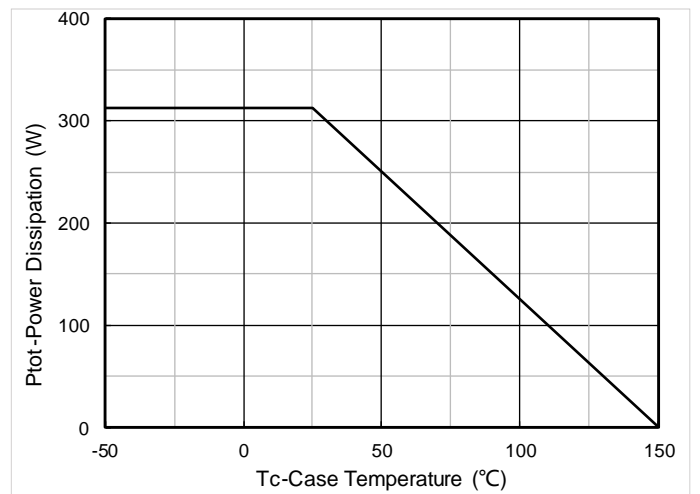


Figure12. Power dissipation

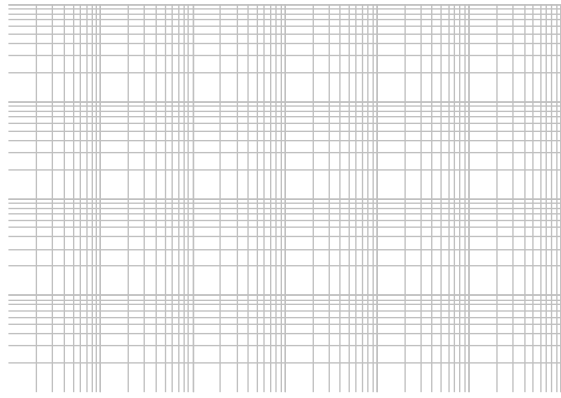


Figure13. Maximum Transient Thermal Impedance

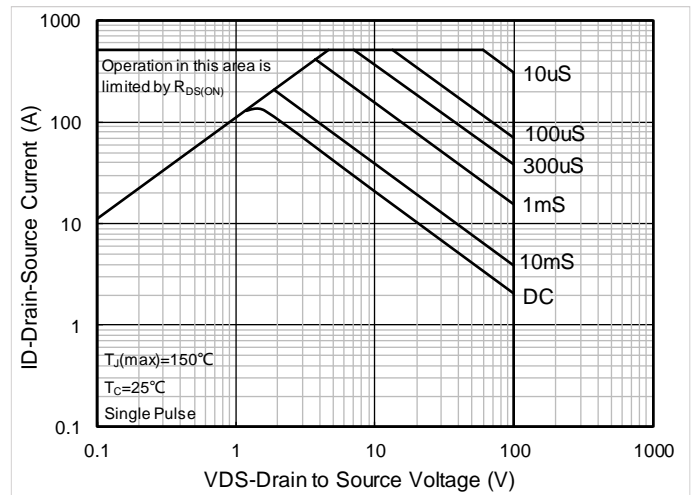
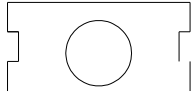


Figure14. Safe Operation Area



TO-220AB-D Package information



NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.



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